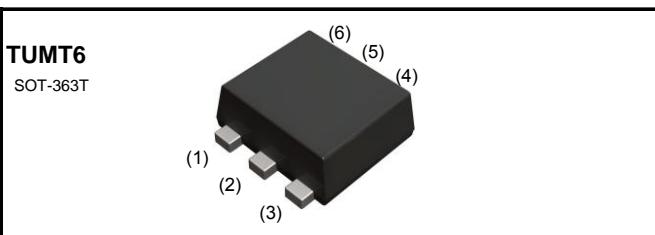


$V_{DSS}$	-30V
$R_{DS(on)}$ (Max.)	50m $\Omega$
$I_D$	-3.5A
$P_D$	1.0W

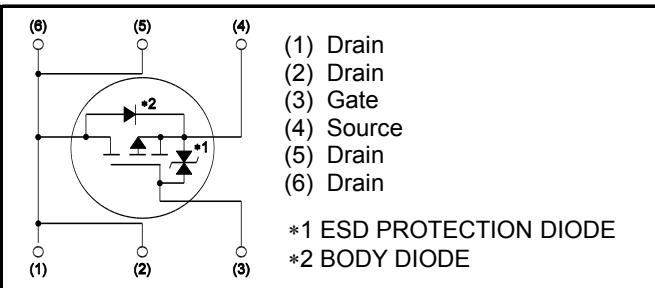
### ●Features

- 1) Low on - resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small Surface Mount Package (TUMT6).
- 4) Pb-free lead plating ; RoHS compliant

### ●Outline



### ●Inner circuit



### ●Packaging specifications

Type	Packaging	Taping
	Reel size (mm)	180
	Tape width (mm)	8
	Basic ordering unit (pcs)	3,000
	Taping code	TR
	Marking	UF

### ●Absolute maximum ratings( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Drain - Source voltage	$V_{DSS}$	-30	V
Continuous drain current	$I_D$ <sup>*1</sup>	$\pm 3.5$	A
Pulsed drain current	$I_{D,pulse}^{*2}$	$\pm 14$	A
Gate - Source voltage	$V_{GSS}$	$\pm 20$	V
Power dissipation	$P_D$ <sup>*3</sup>	1.0	W
	$P_D$ <sup>*4</sup>	0.32	W
Junction temperature	$T_j$	150	$^\circ\text{C}$
Range of storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

● Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - ambient	$R_{thJA}^{*3}$	-	-	125	°C/W
	$R_{thJA}^{*4}$	-	-	391	°C/W

● Electrical characteristics ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{V}, I_D = -1\text{mA}$	-30	-	-	V
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_j}$	$I_D = -1\text{mA}$ referenced to $25^\circ\text{C}$	-	-25	-	mV/°C
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = -30\text{V}, V_{GS} = 0\text{V}$	-	-	-1	μA
Gate - Source leakage current	$I_{GSS}$	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$	-	-	$\pm 10$	μA
Gate threshold voltage	$V_{GS(\text{th})}$	$V_{DS} = -10\text{V}, I_D = -1\text{mA}$	-1.0	-	-2.5	V
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{(GS)\text{th}}}{\Delta T_j}$	$I_D = b - 1\text{mA}$ referenced to $25^\circ\text{C}$	-	3.9	-	mV/°C
Static drain - source on - state resistance	$R_{DS(on)}^{*5}$	$V_{GS} = -10\text{V}, I_D = -3.5\text{A}$	-	36	50	mΩ
		$V_{GS} = -4.5\text{V}, I_D = -1.7\text{A}$	-	52	72	
		$V_{GS} = -4.0\text{V}, I_D = -1.7\text{A}$	-	58	81	
		$V_{GS} = -10\text{V}, I_D = -3.5\text{A}, T_j = 125^\circ\text{C}$	-	52	73	
Gate input resistancce	$R_G$	f = 1MHz, open drain	-	19	-	Ω
Transconductance	$g_{fs}^{*5}$	$V_{DS} = -10\text{V}, I_D = -3.5\text{A}$	2.3	6.5	-	S

\*1 Limited only by maximum temperature allowed.

\*2  $P_w \leq 10\mu\text{s}$ , Duty cycle  $\leq 1\%$

\*3 Mounted on a ceramic board (30×30×0.8mm)

\*4 Mounted on a FR4 (15×20×0.8mm)

\*5 Pulsed

● Electrical characteristics( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{V}$ $V_{DS} = -10\text{V}$ $f = 1\text{MHz}$	-	800	-	pF
Output capacitance	$C_{oss}$		-	120	-	
Reverse transfer capacitance	$C_{rss}$		-	110	-	
Turn - on delay time	$t_{d(on)}^{*5}$	$V_{DD} \approx -15\text{V}, V_{GS} = -10\text{V}$ $I_D = -1.7\text{A}$ $R_L = 8.8\Omega$ $R_G = 10\Omega$	-	7	-	ns
Rise time	$t_r^{*5}$		-	9	-	
Turn - off delay time	$t_{d(off)}^{*5}$		-	75	-	
Fall time	$t_f^{*5}$		-	40	-	

● Gate Charge characteristics( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	$Q_g^{*5}$	$V_{DD} \approx -15\text{V}, I_D = -3.5\text{A}$ $V_{GS} = -5\text{V}$	-	8.0	-	nC
		$V_{DD} \approx -15\text{V}, I_D = -3.5\text{A}$ $V_{GS} = -10\text{V}$	-	14	-	
Gate - Source charge	$Q_{gs}^{*5}$	$V_{DD} \approx -15\text{V}, I_D = -3.5\text{A}$ $V_{GS} = -5\text{V}$	-	2.5	-	
Gate - Drain charge	$Q_{gd}^{*5}$		-	3.0	-	

● Body diode electrical characteristics (Source-Drain)( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Inverse diode continuous, forward current	$I_S^{*1}$	$T_a = 25^\circ\text{C}$	-	-	-0.8	A
Forward voltage	$V_{SD}^{*5}$	$V_{GS} = 0\text{V}, I_s = -3.5\text{A}$	-	-	-1.2	V

## ● Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

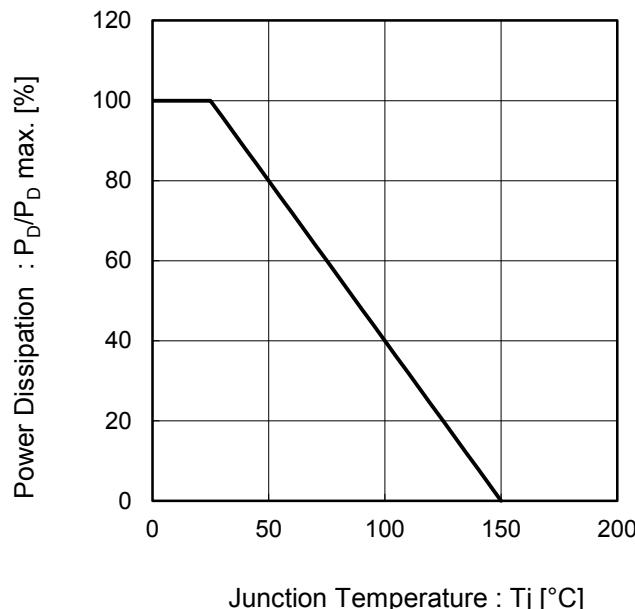


Fig.2 Maximum Safe Operating Area

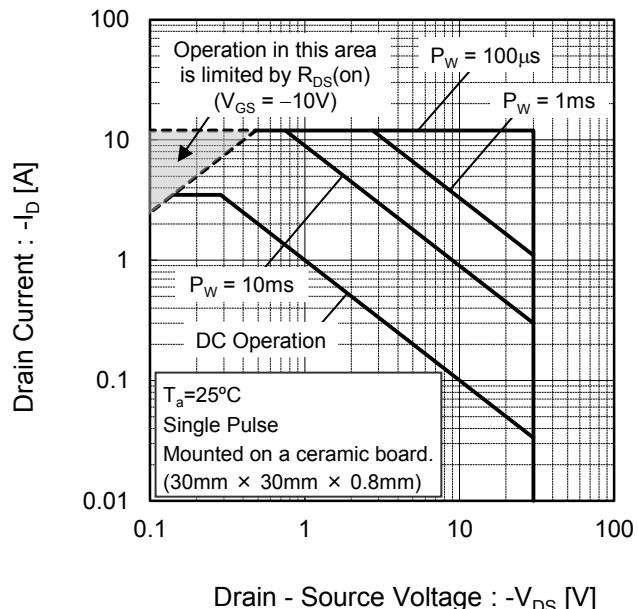


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

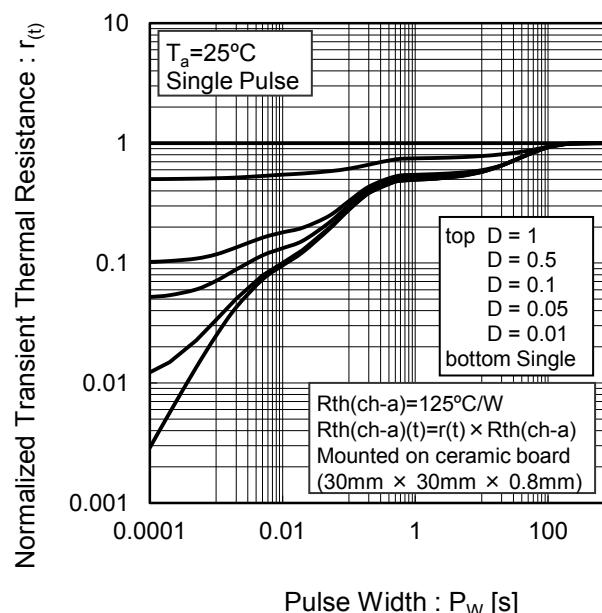
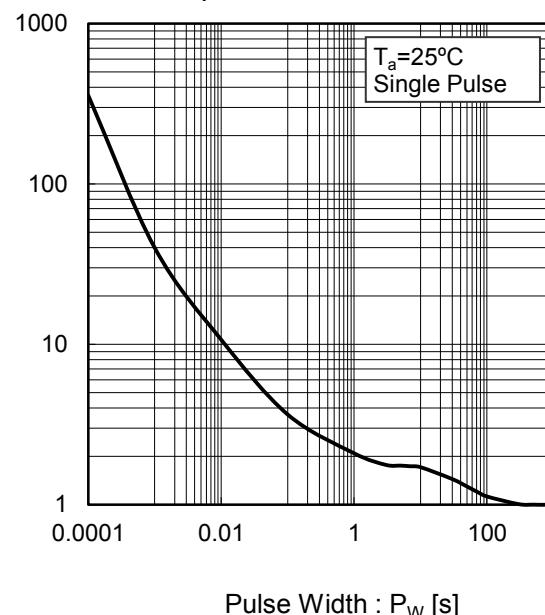


Fig.4 Single Pulse Maximum Power dissipation



●Electrical characteristic curves

Fig.5 Typical Output Characteristics(I)

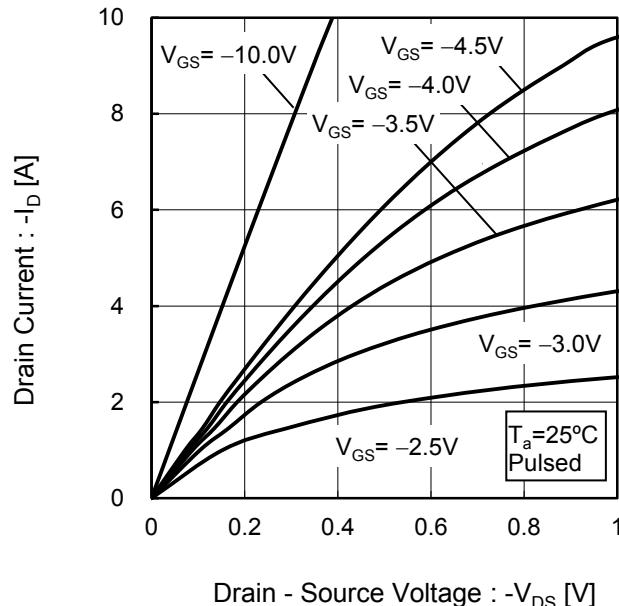


Fig.6 Typical Output Characteristics(II)

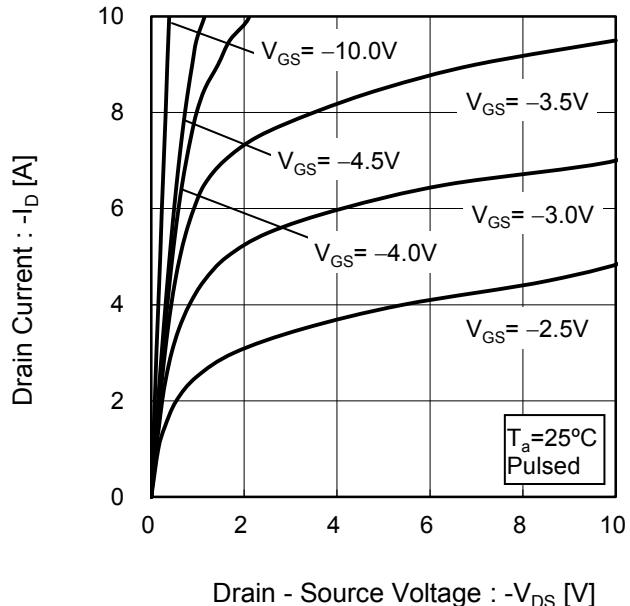


Fig.7 Breakdown Voltage  
vs. Junction Temperature

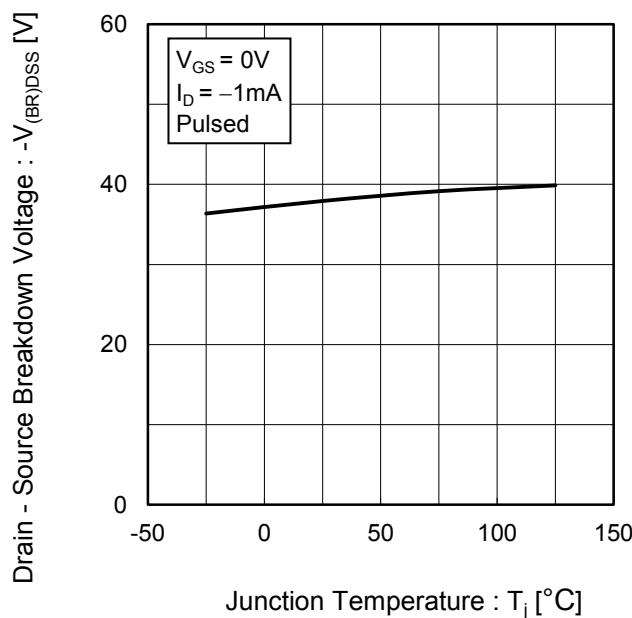
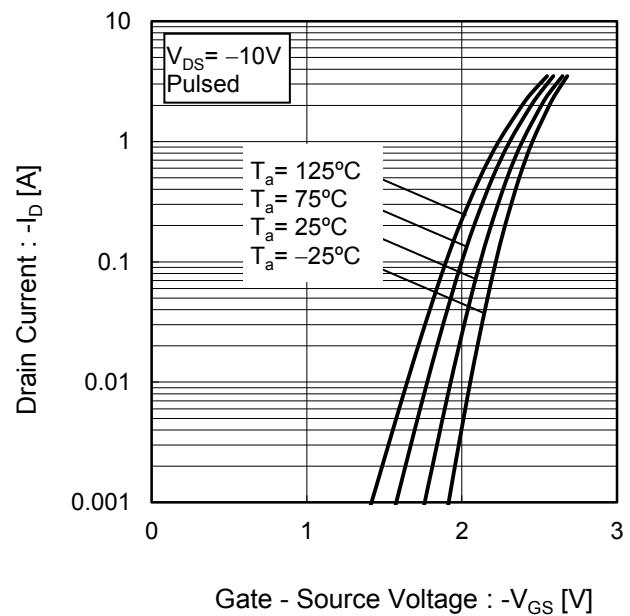


Fig.8 Typical Transfer Characteristics



● Electrical characteristic curves

Fig.9 Gate Threshold Voltage vs. Junction Temperature

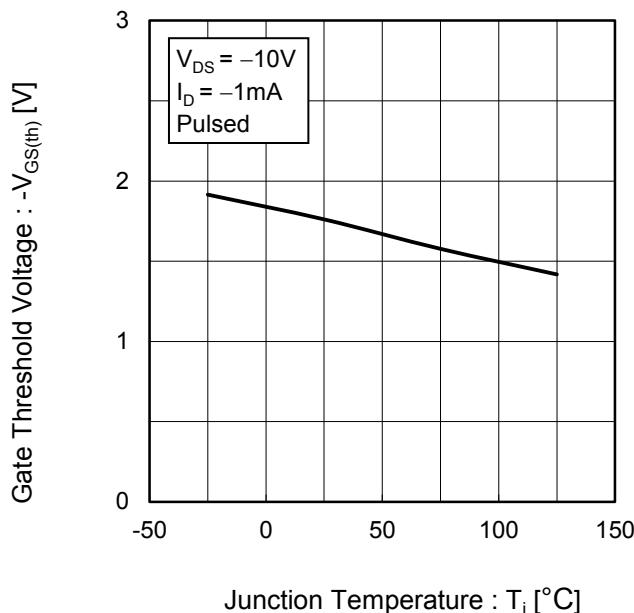


Fig.10 Transconductance vs. Drain Current

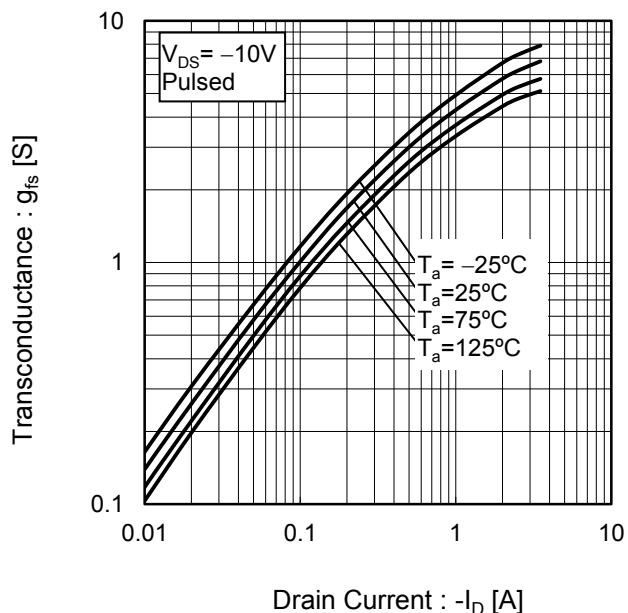


Fig.11 Drain CurrentDerating Curve

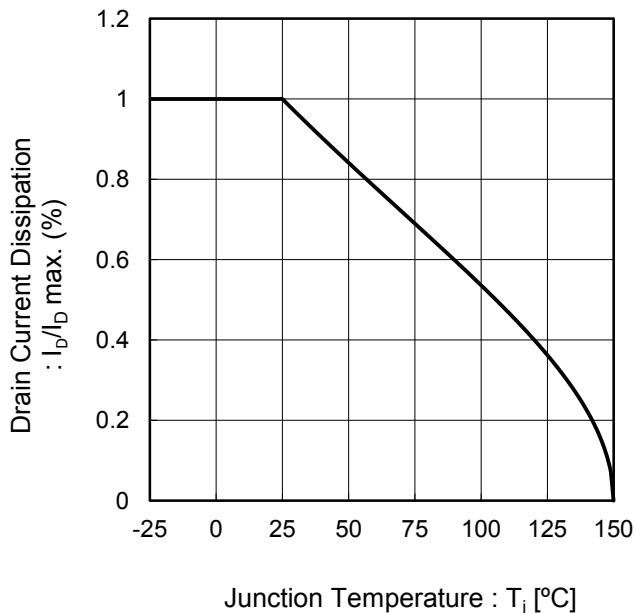
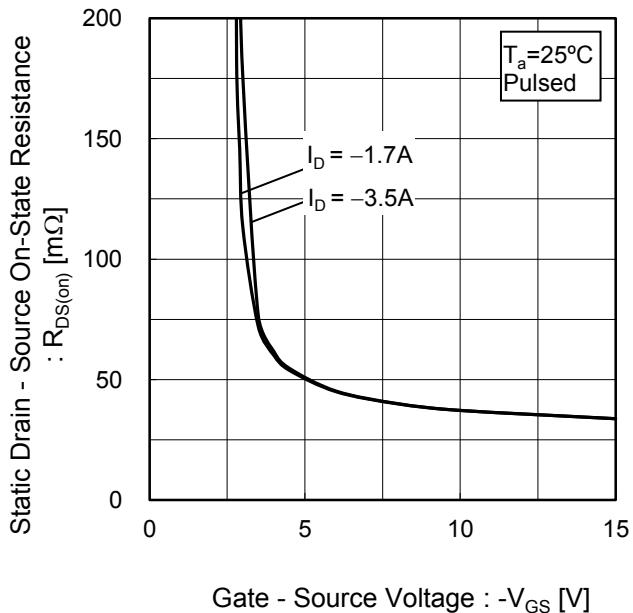


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage



● Electrical characteristic curves

Fig.13 Static Drain - Source On - State Resistance vs. Drain Current( $I_D$ )

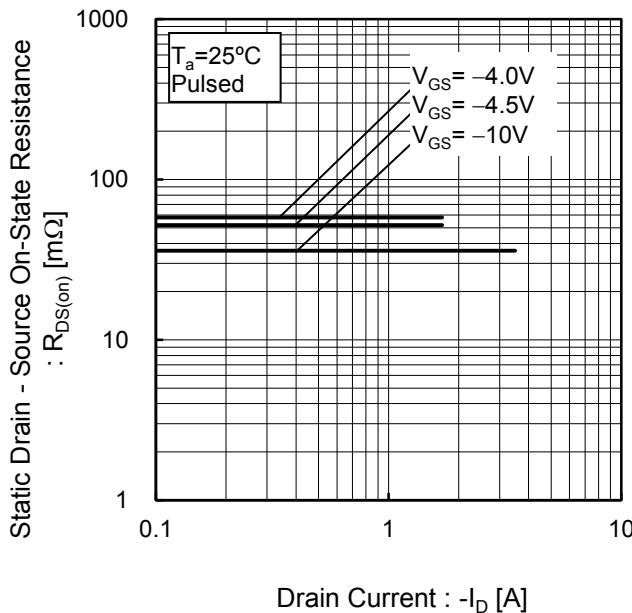


Fig.14 Static Drain - Source On - State Resistance vs. Junction Temperature

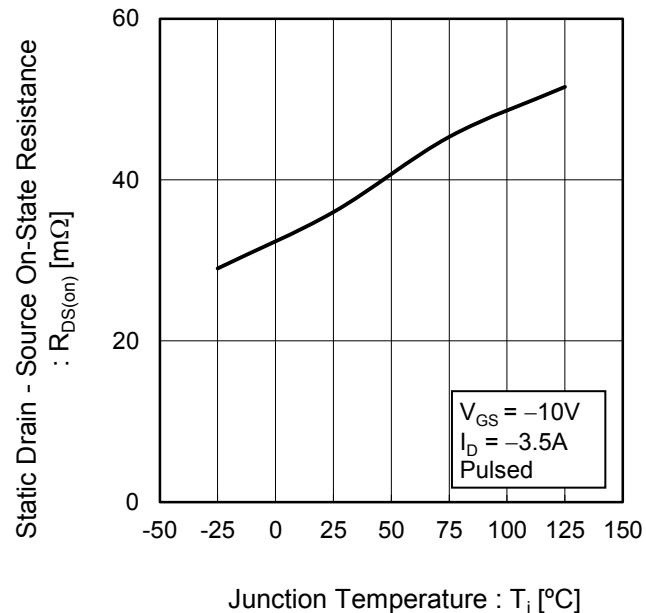


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(II)

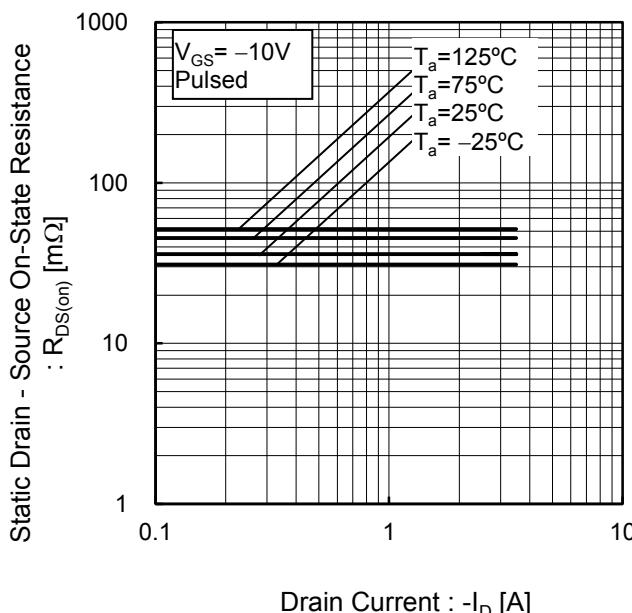
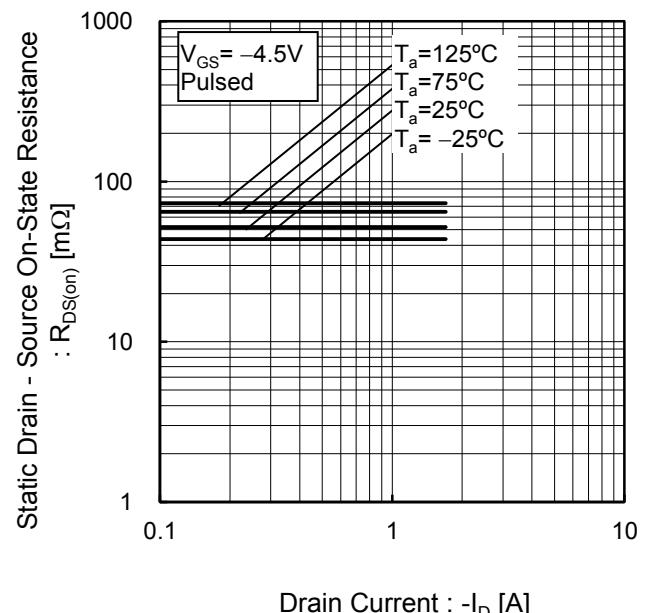


Fig.16 Static Drain-Source On-State Resistance vs. Drain Current(III)



● Electrical characteristic curves

Fig.17 Static Drain - Source On - State Resistance vs. Drain Current(IV)

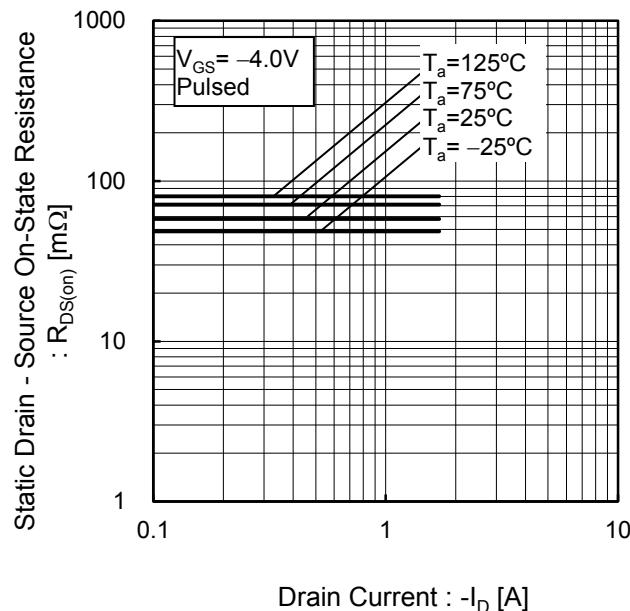


Fig.18 Typical Capacitance vs. Drain - Source Voltage

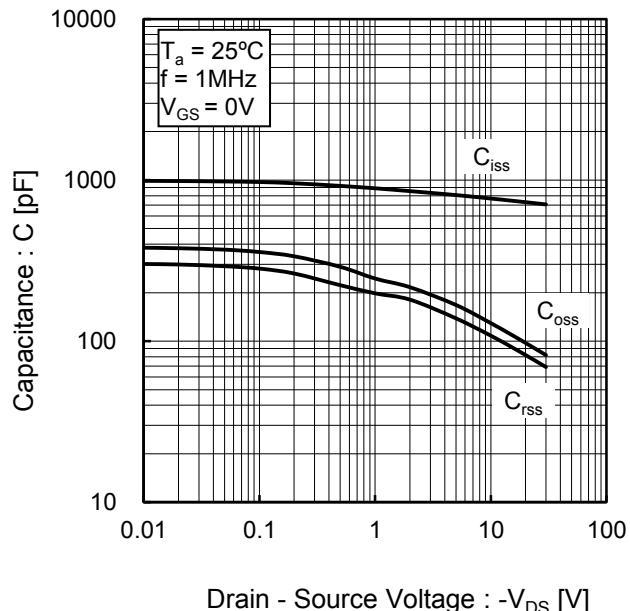


Fig.19 Switching Characteristics

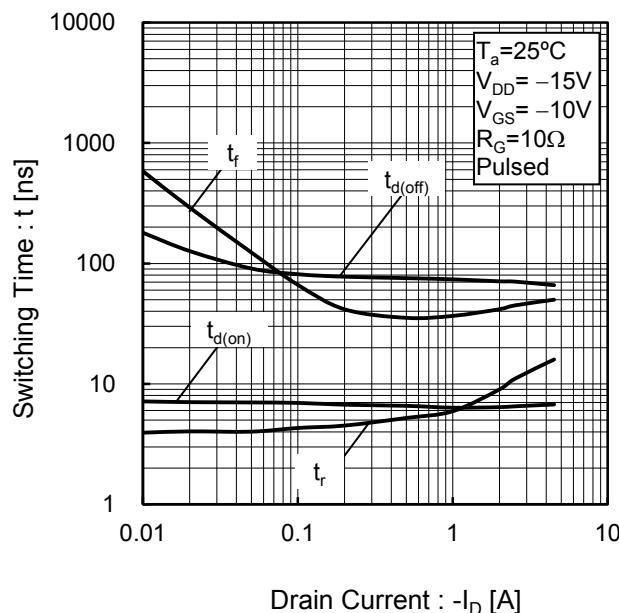
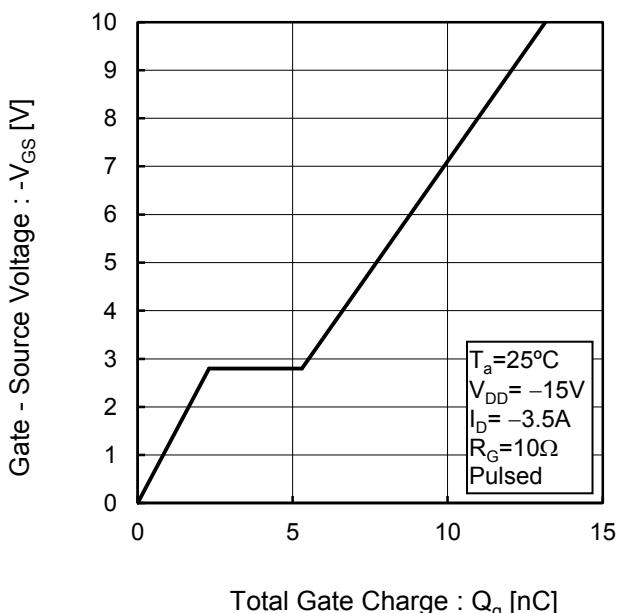
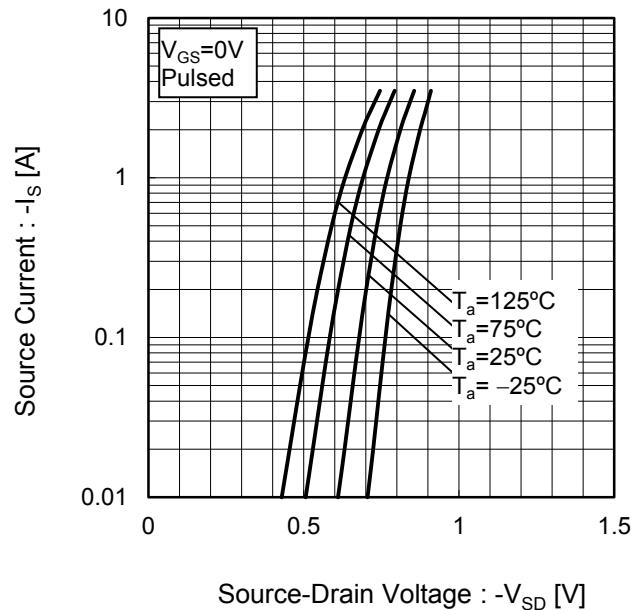


Fig.20 Dynamic Input Characteristics



**●Electrical characteristic curves**

Fig.21 Source Current  
vs. Source Drain Voltage



## ●Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

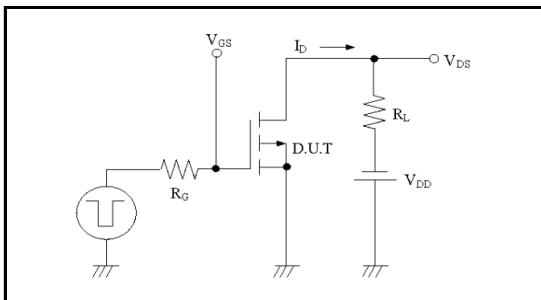


Fig.1-2 Switching Waveforms

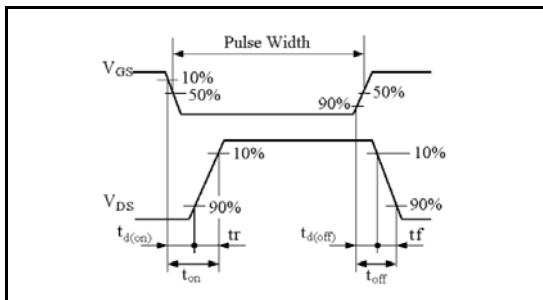


Fig.2-1 Gate Charge Measurement Circuit

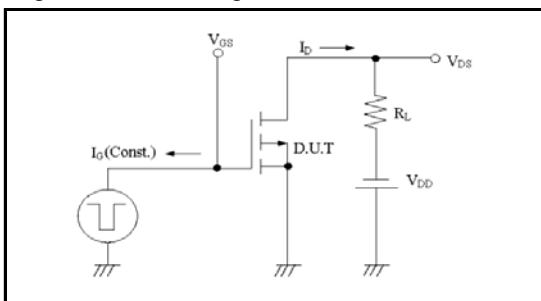
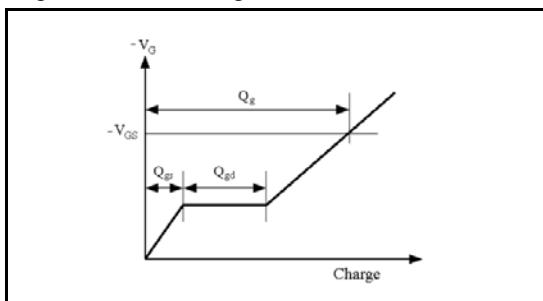
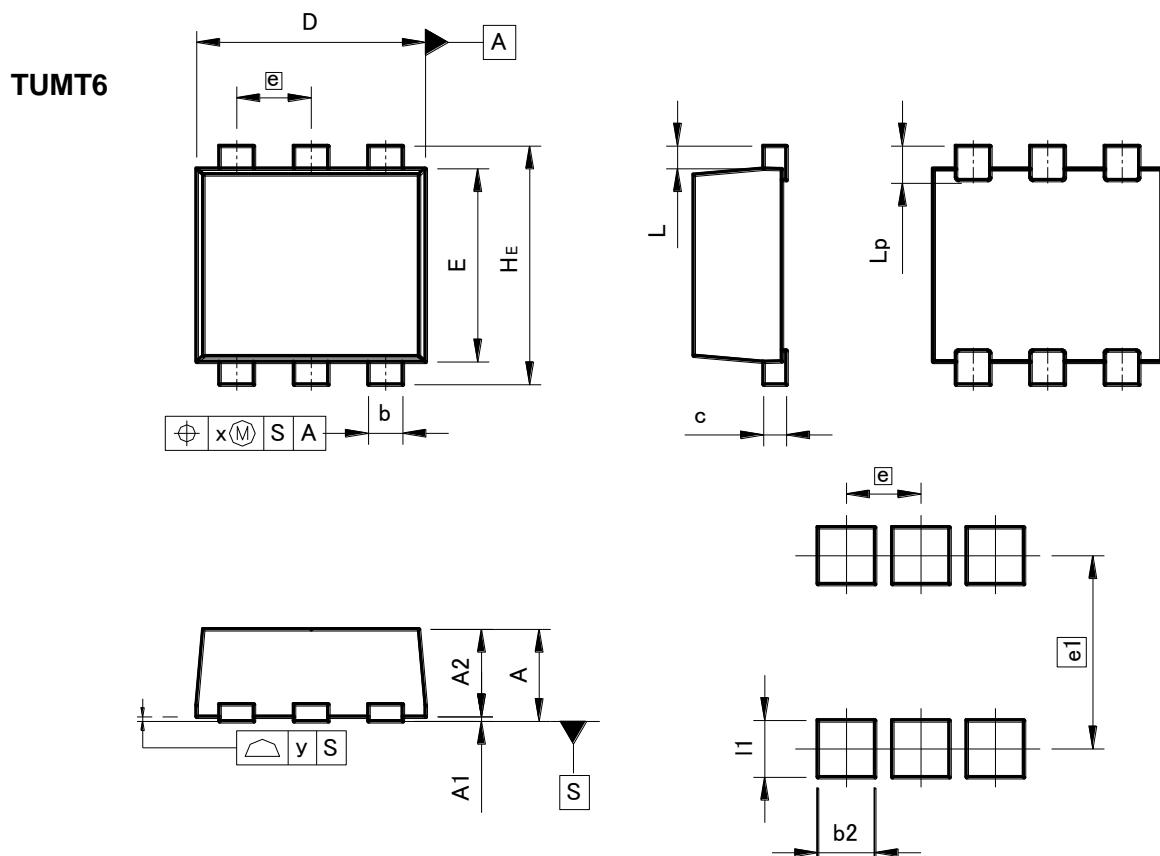


Fig.2-2 Gate Charge Waveform



●Dimensions (Unit : mm)



Pattern of terminal position areas

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	—	0.85	—	0.033
A1	0.00	0.10	0	0.004
A2	0.72	0.82	0.028	0.032
b	0.25	0.40	0.01	0.016
c	0.12	0.22	0.005	0.009
D	1.90	2.10	0.075	0.083
E	1.60	1.80	0.063	0.071
e	0.65		0.03	
HE	2.00	2.20	0.079	0.087
L	0.20		0.01	
Lp	—	0.40	—	0.016
x	—	0.10	—	0.004
y	—	0.10	—	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
e1	1.70		0.067	
b2	—	0.50	—	0.02
l1	—	0.50	—	0.02

Dimension in mm/inches

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